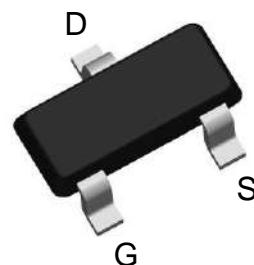


P-Channel Enhancement Mode MOSFET

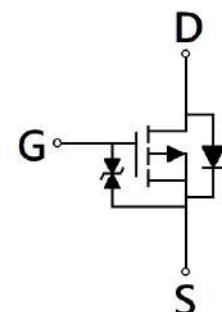
Features:

- Low On Resistance
- Low Gate Charge
- Fast Switching Characteristic
- ESD protected gate, typical 4kV (HBM)

SOT-523



BVDSS	-20V
ID@VGS=-4.5V, TA=25°C	-0.84A
RDS(ON) typ. @ VGS=-4.5V, ID=-0.4A	0.75Ω
RDS(ON) typ. @ VGS=-2.5V, ID=-0.3A	1.0Ω
RDS(ON) typ. @ VGS=-1.8V, ID=-10mA	1.2Ω



G : Gate S : Source D : Drain

Ordering Information

Device	Package	Shipping
KWA600P02K-5	SOT-523 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel



Absolute Maximum Ratings ($T_A=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current @ $V_{GS}=-4.5\text{V}$, $T_A=25^\circ\text{C}$	I_D	-0.84	A
Continuous Drain Current @ $V_{GS}=-4.5\text{V}$, $T_A=70^\circ\text{C}$		-0.67	
Pulsed Drain Current	I_{DM}	-3.4	
Continuous Body Diode Forward Current @ $T_A=25^\circ\text{C}$	I_S	-1	
ESD susceptibility	V_{ESD}	4000	V
Total Power Dissipation @ $T_A=25^\circ\text{C}$	P_D	1.3	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Steady State	Unit
Thermal Resistance, Junction-to-ambient	$R_{\theta JA}$	96	°C/W

Note:

*a. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$. Ratings are based on low frequency and low duty cycles to keep initial $T_J=25^\circ\text{C}$.

*b. Human body model, $1.5\text{k}\Omega$ in series with 100pF .

Electrical Characteristics ($T_A=25^\circ\text{C}$, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	-20	-	-	V	V _{GS} =0V, I _D =-250μA
V _{GS(th)}	-0.3	-	-1.0		V _{DS} =V _{GS} , I _D =-250μA
G _{FS}	-	1	-	S	V _{DS} =-5V, I _D =-0.4A
I _{GSS}	-	-	±10		V _{GS} =±8V, V _{DS} =0V
I _{DSS}	-	-	-1	μA	V _{DS} =-16V, V _{GS} =0V
R _{DSON}	-	0.75	1.1		V _{GS} =-4.5V, I _D =-0.4A
	-	1.0	1.5		V _{GS} =-2.5V, I _D =-0.3A
	-	1.2	2.5		V _{GS} =-1.8V, I _D =-10mA
Dynamic					
C _{iss}	-	45	-	pF	V _{DS} =-10V, V _{GS} =0V, f=1MHz
C _{oss}	-	15	-		
C _{rss}	-	5.6	-		
Q _g *1, 2	-	1	-	nC	V _{DS} =-20V, I _D =-0.4A, V _{GS} =-4.5V
Q _{gs} *1, 2	-	0.2	-		
Q _{gd} *1, 2	-	0.2	-		
t _{d(ON)} *1, 2	-	11	-	ns	V _{DS} =-10V, I _D =-0.4A, V _{GS} =-4.5V, R _{GS} =1Ω
t _r *1, 2	-	19	-		
t _{d(OFF)} *1, 2	-	43	-		
t _f *1, 2	-	28	-		
Source-Drain Diode					
V _{SD} *1	-	-0.92	-1.2	V	I _S =-0.4A, V _{GS} =0V

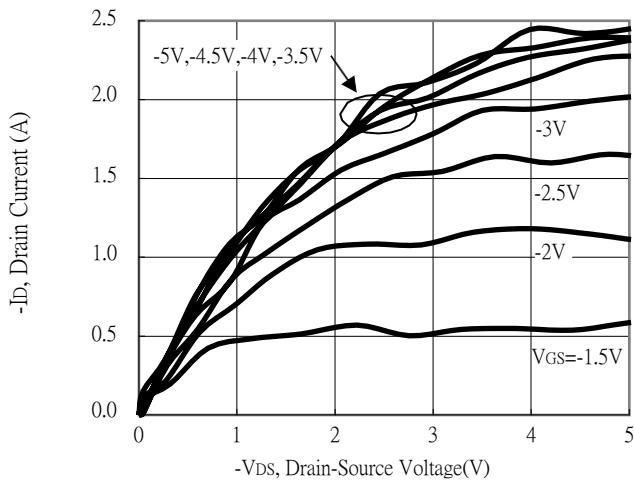
Note:

*1. Pulse Test : Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

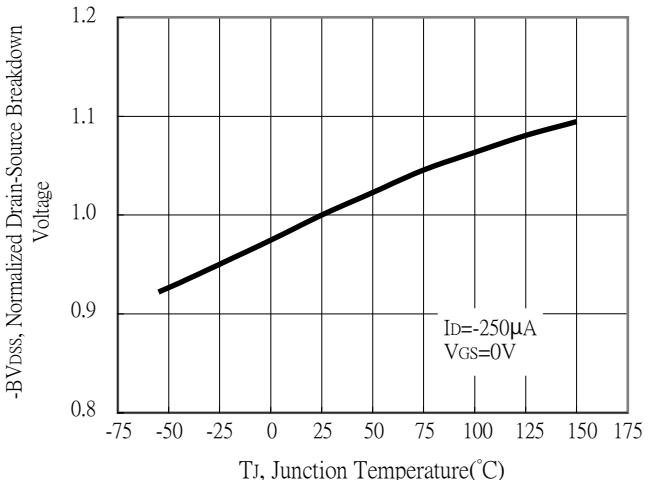
*2. Independent of operating temperature

Typical Characteristics

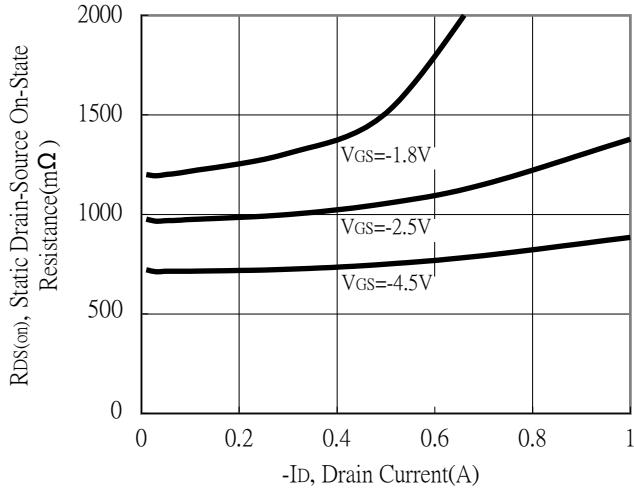
Typical Output Characteristics



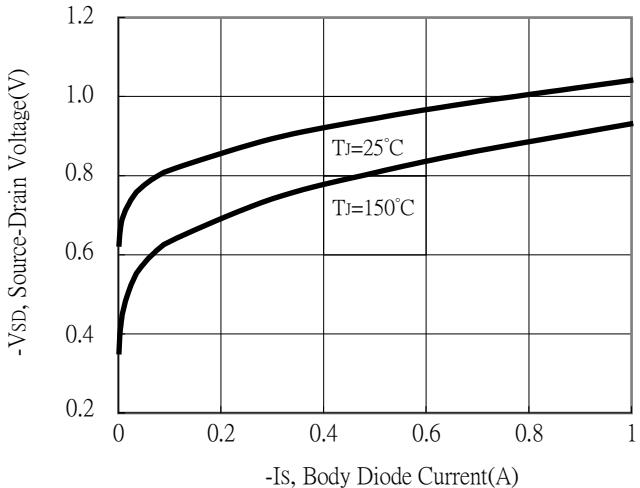
Breakdown Voltage vs Junction Temperature



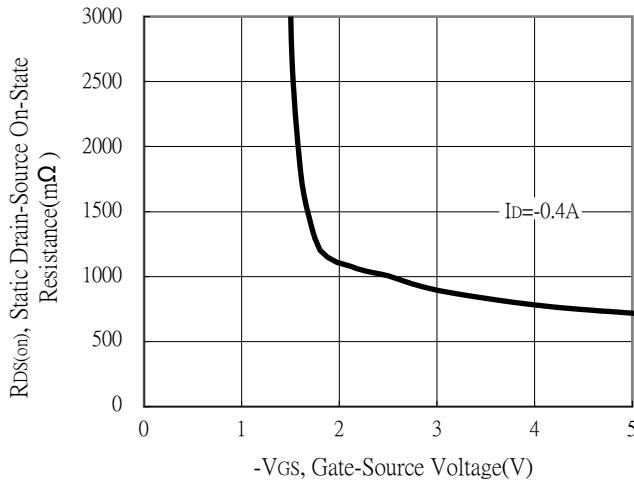
Static Drain-Source On-State resistance vs Drain Current



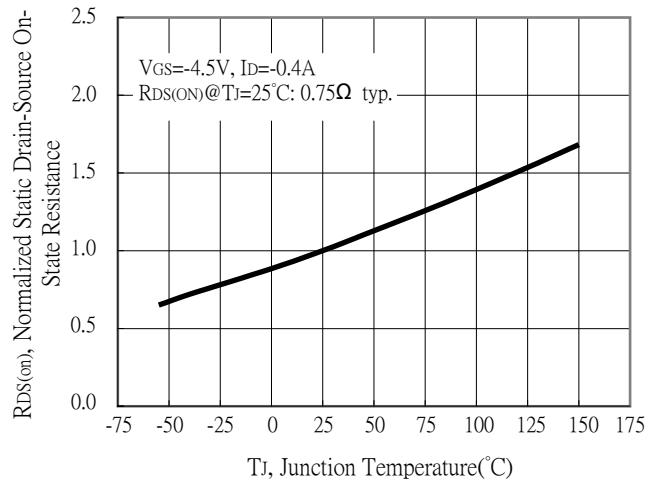
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

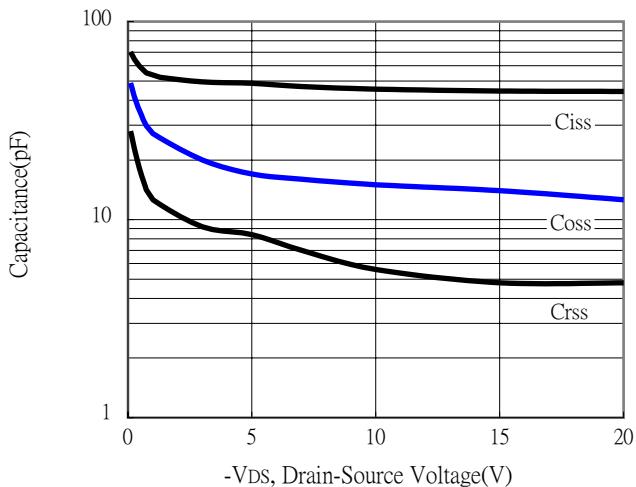


Drain-Source On-State Resistance vs Junction Temperature

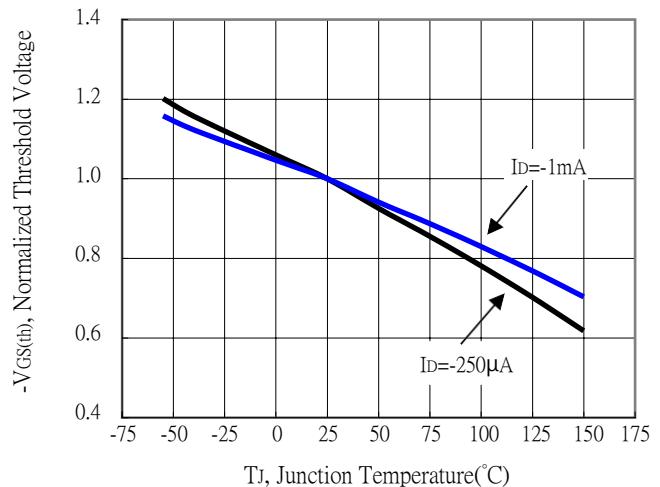


Typical Characteristics (Cont.)

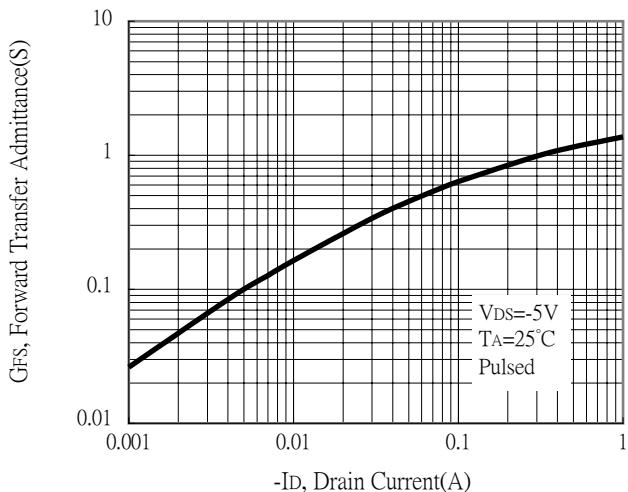
Capacitance vs Drain-to-Source Voltage



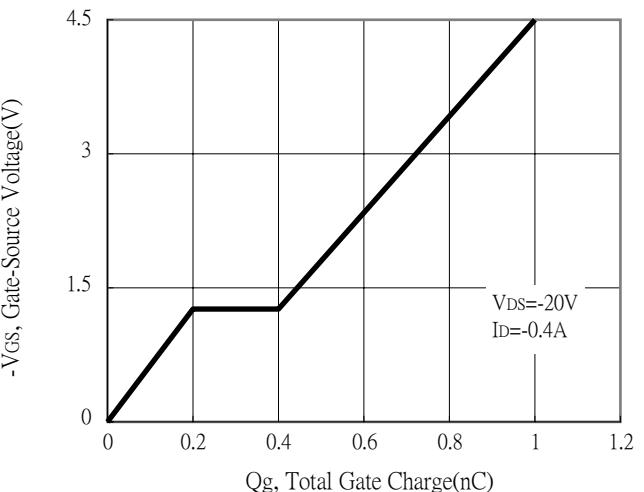
Threshold Voltage vs Junction Temperature



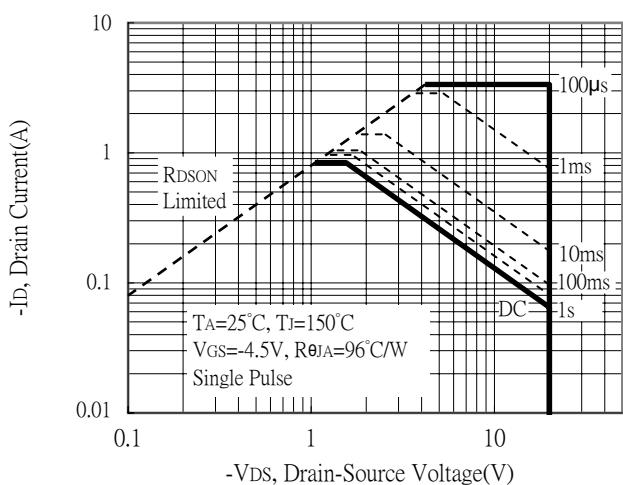
Forward Transfer Admittance vs Drain Current



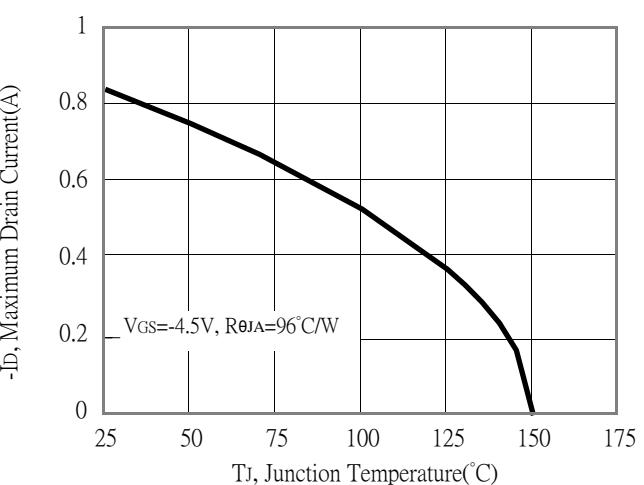
Gate Charge Characteristics



Maximum Safe Operating Area

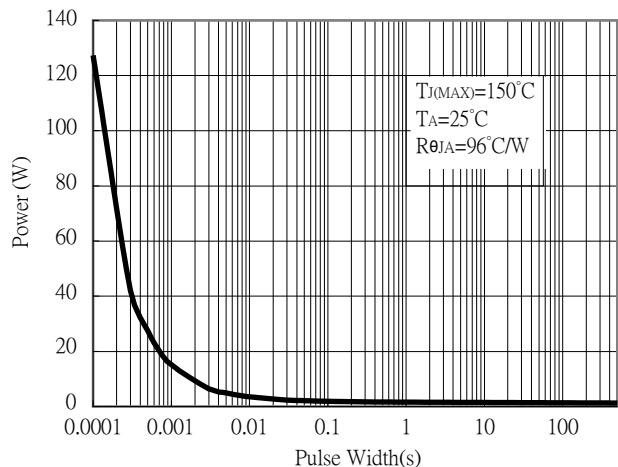


Maximum Drain Current vs Junction Temperature

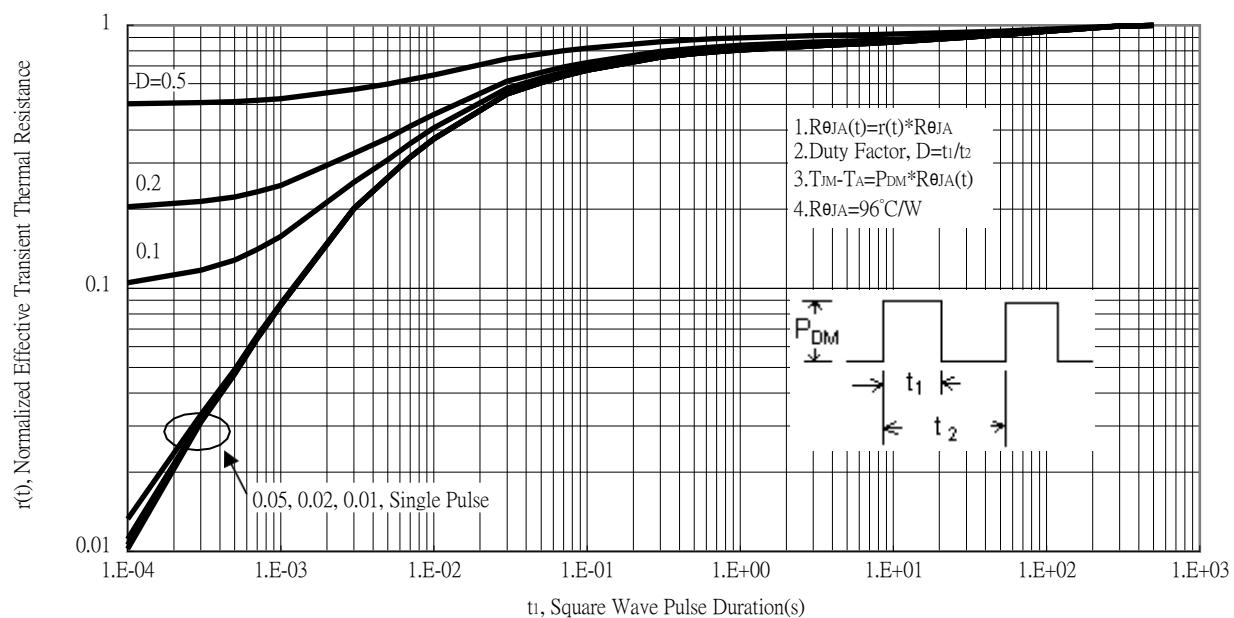


Typical Characteristics (Cont.)

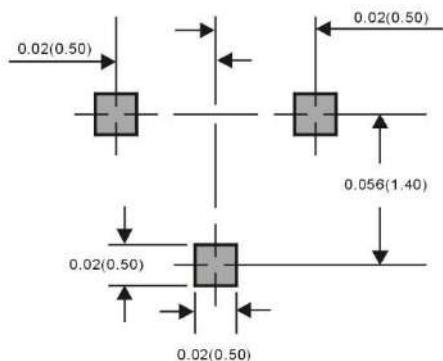
Single Pulse Power Rating, Junction to Ambient



Transient Thermal Response Curves

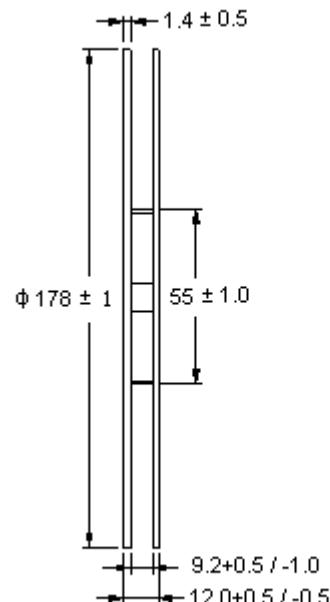
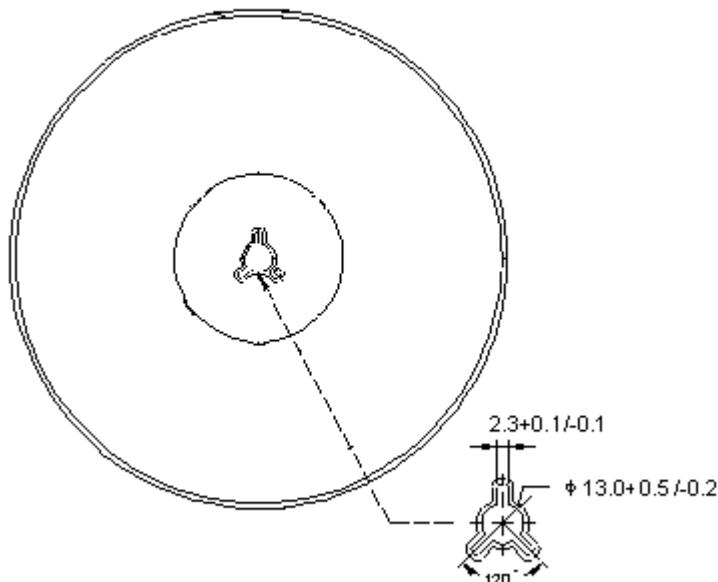


Recommended Soldering Footprint



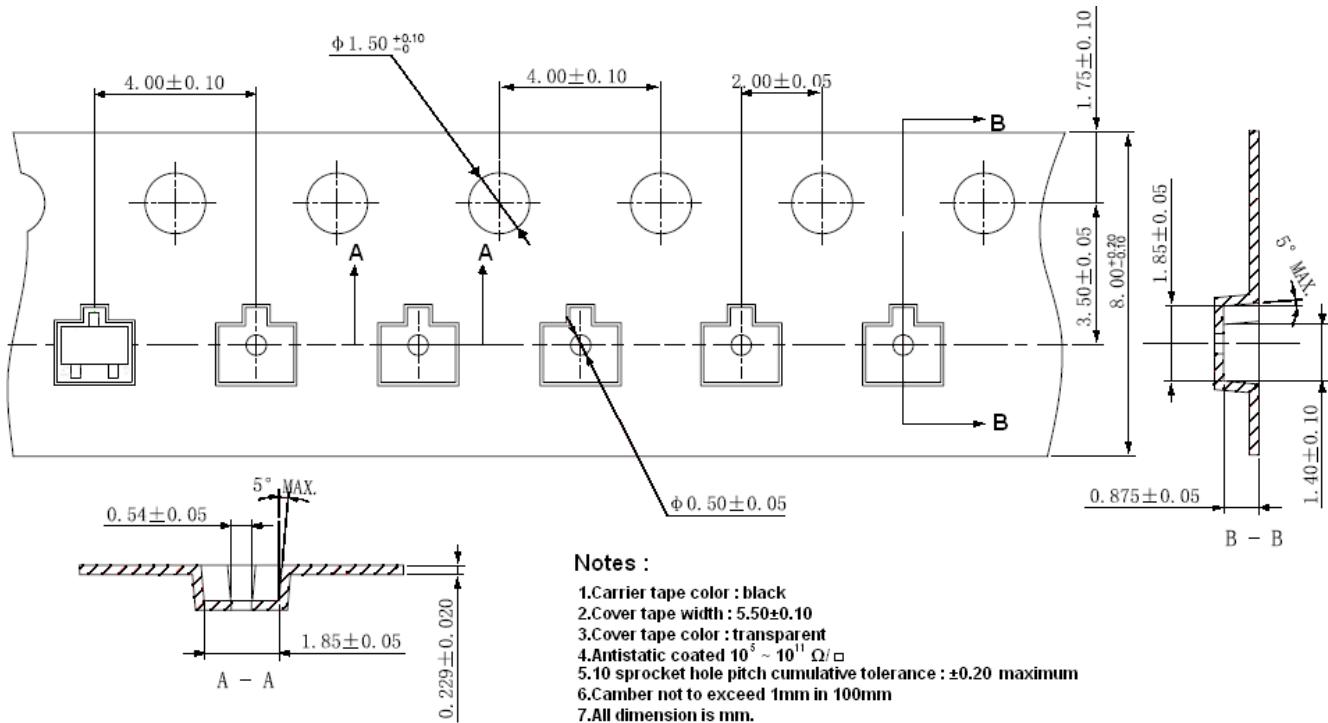
Dimensions in inches and (millimeters)

Reel Dimension

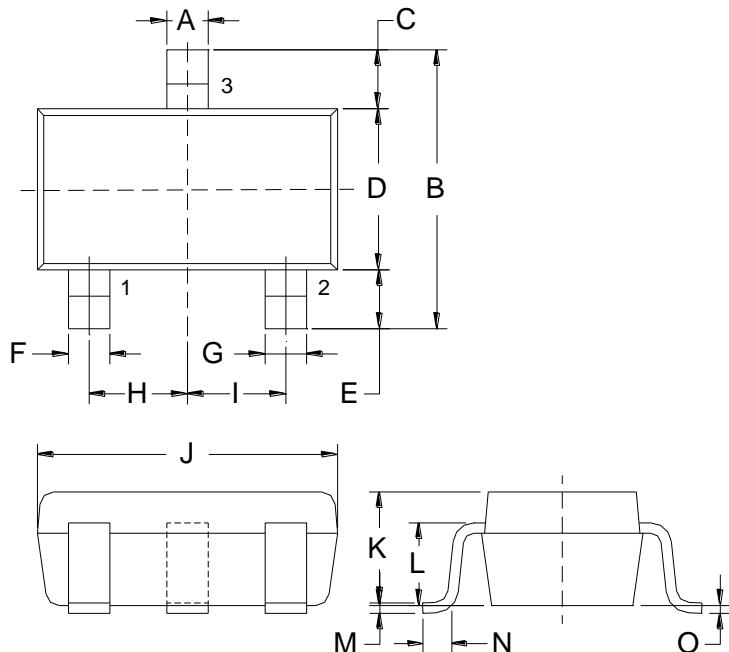


Unit: millimeter

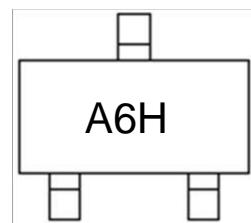
Carrier Tape Dimension



SOT-523 Dimension



Marking:



3-Lead SOT-523 Plastic
Surface Mounted Package

Style: Pin 1.Gate 2.Source 3.Drain

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.0079	0.0157	0.20	0.40	I	*0.0197	-	*0.50	-
B	0.0591	0.0669	1.50	1.70	J	0.0610	0.0650	1.55	1.65
C	0.0118	0.0197	0.30	0.50	K	0.0276	0.0315	0.70	0.80
D	0.0295	0.0335	0.75	0.85	L	0.0224	0.0248	0.57	0.63
E	0.0118	0.0197	0.30	0.50	M	0.0020	0.0059	0.05	0.15
F	0.0039	0.0118	0.10	0.30	N	0.0039	0.0118	0.10	0.30
G	0.0039	0.0118	0.10	0.30	O	0	0.0031	0	0.08
H	*0.0197	-	*0.50	-					